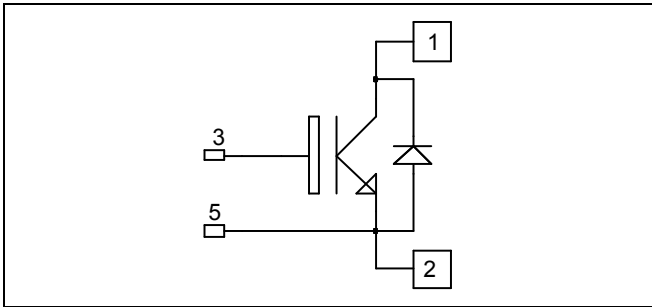


**Single switch  
Trench + Field Stop IGBT3  
Power Module**

**$V_{CES} = 600V$   
 $I_C = 750A @ T_c = 80^\circ C$**



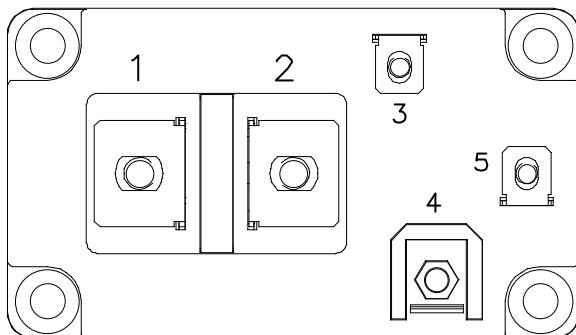
### Application

- Welding converters
- Switched Mode Power Supplies
- Uninterruptible Power Supplies
- Motor control

### Features

- Trench + Field Stop IGBT3 Technology
  - Low voltage drop
  - Low tail current
  - Switching frequency up to 20 kHz
  - Soft recovery parallel diodes
  - Low diode VF
  - Low leakage current
  - RBSOA and SCSOA rated

- Kelvin emitter for easy drive
- M6 connectors for power
- M4 connectors for signal
- High level of integration



### Benefits

- Stable temperature behavior
- Very rugged
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Easy paralleling due to positive  $T_C$  of  $V_{CEsat}$
- RoHS Compliant

### Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
$V_{CES}$	Collector - Emitter Breakdown Voltage	600	V
$I_C$	Continuous Collector Current	$T_C = 25^\circ C$	1000
		$T_C = 80^\circ C$	750
$I_{CM}$	Pulsed Collector Current	$T_C = 25^\circ C$	1000
$V_{GE}$	Gate - Emitter Voltage	$\pm 20$	V
$P_D$	Maximum Power Dissipation	$T_C = 25^\circ C$	2300
RBSOA	Reverse Bias Safe Operating Area	$T_j = 125^\circ C$	1600A@550V

**CAUTION:** These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed. See application note APT0502 on [www.microsemi.com](http://www.microsemi.com)

All ratings @  $T_j = 25^\circ\text{C}$  unless otherwise specified

**Electrical Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{CES}$	Zero Gate Voltage Collector Current	$V_{GE} = 0V, V_{CE} = 600V$			1	mA
$V_{CE(sat)}$	Collector Emitter saturation Voltage	$V_{GE} = 15V$ $I_C = 800A$	$T_j = 25^\circ\text{C}$	1.5	1.9	V
			$T_j = 125^\circ\text{C}$		1.7	
$V_{GE(th)}$	Gate Threshold Voltage	$V_{GE} = V_{CE}, I_C = 13mA$	5.0	5.8	6.5	V
$I_{GES}$	Gate – Emitter Leakage Current	$V_{GE} = 20V, V_{CE} = 0V$			3100	nA

**Dynamic Characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$C_{ies}$	Input Capacitance	$V_{GE} = 0V$ $V_{CE} = 25V$ $f = 1MHz$		49		nF
$C_{oes}$	Output Capacitance			3.1		
$C_{res}$	Reverse Transfer Capacitance			1.5		
$Q_G$	Gate charge	$V_{GE} = -8/+15V, I_C = 800A$ $V_{CE} = 300V$		5.8		$\mu\text{C}$
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $25^\circ\text{C}$ ) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 800A$ $R_G = 2\Omega$		250		ns
$T_r$	Rise Time			70		
$T_{d(off)}$	Turn-off Delay Time			550		
$T_f$	Fall Time			70		
$T_{d(on)}$	Turn-on Delay Time	Inductive Switching ( $150^\circ\text{C}$ ) $V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 800A$ $R_G = 2\Omega$		270		ns
$T_r$	Rise Time			80		
$T_{d(off)}$	Turn-off Delay Time			650		
$T_f$	Fall Time			80		
$E_{on}$	Turn on Energy	$V_{GE} = \pm 15V$ $V_{Bus} = 300V$ $I_C = 800A$ $R_G = 2\Omega$	$T_j = 150^\circ\text{C}$		10	mJ
$E_{off}$	Turn off Energy			$T_j = 150^\circ\text{C}$	40	
$I_{sc}$	Short Circuit data	$V_{GE} \leq 15V; V_{Bus} = 360V$ $t_b = 6\mu\text{s}; T_j = 150^\circ\text{C}$		4000		A

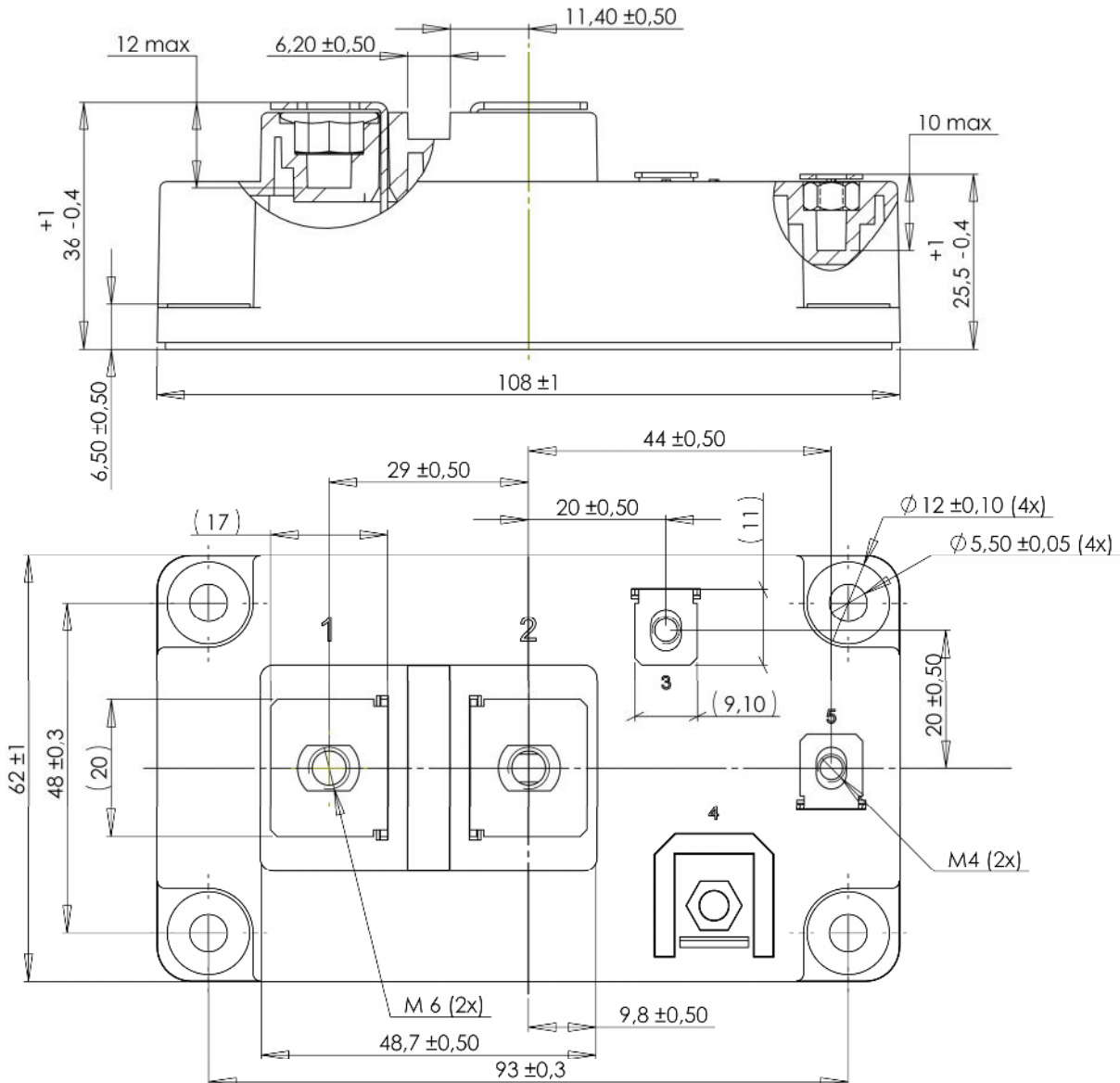
**Reverse diode ratings and characteristics**

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$V_{RRM}$	Maximum Peak Repetitive Reverse Voltage		600			V
$I_{RRM}$	Maximum Reverse Leakage Current	$V_R = 600V$	$T_j = 25^\circ\text{C}$		750	$\mu\text{A}$
			$T_j = 150^\circ\text{C}$		1000	
$I_F$	DC Forward Current			800		A
$V_F$	Diode Forward Voltage	$I_F = 800A$ $V_{GE} = 0V$	$T_j = 25^\circ\text{C}$	1.6	2.1	V
			$T_j = 150^\circ\text{C}$		1.5	
$t_{rr}$	Reverse Recovery Time	$I_F = 800A$ $V_R = 300V$ $di/dt = 5000A/\mu\text{s}$	$T_j = 25^\circ\text{C}$	150		ns
			$T_j = 150^\circ\text{C}$		250	
$Q_{rr}$	Reverse Recovery Charge	$I_F = 800A$ $V_R = 300V$ $di/dt = 5000A/\mu\text{s}$	$T_j = 25^\circ\text{C}$	36		$\mu\text{C}$
			$T_j = 150^\circ\text{C}$		76	
$E_{rr}$	Reverse Recovery Energy	$I_F = 800A$ $V_R = 300V$ $di/dt = 5000A/\mu\text{s}$	$T_j = 25^\circ\text{C}$	9.2		mJ
			$T_j = 150^\circ\text{C}$		19	

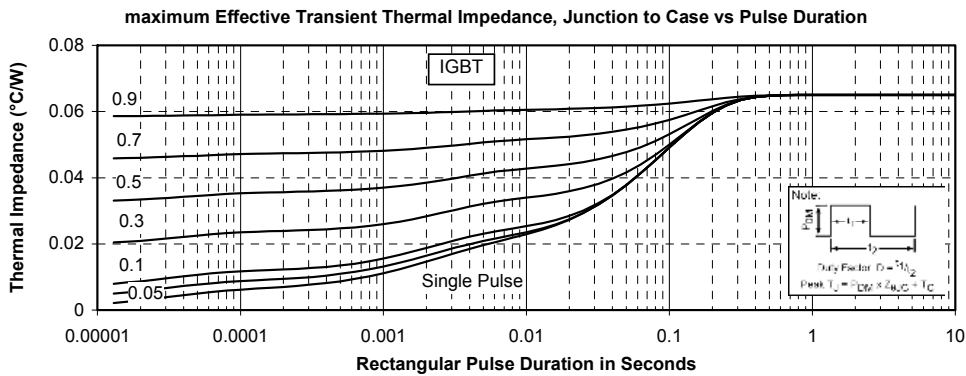
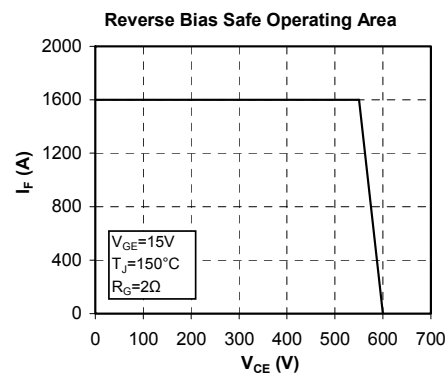
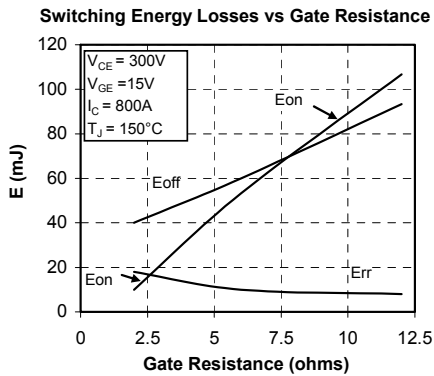
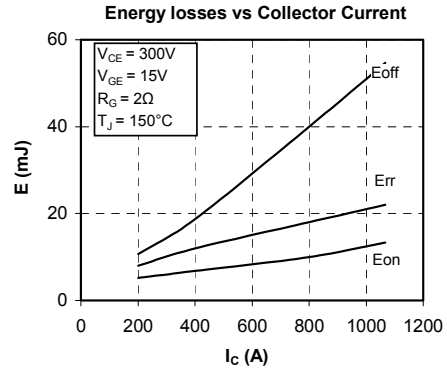
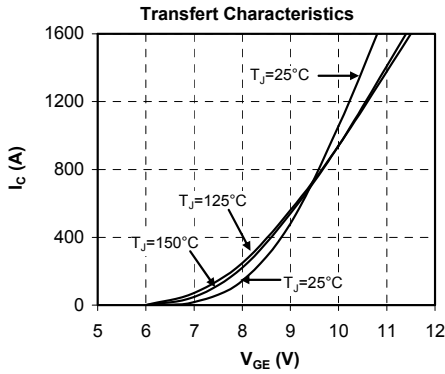
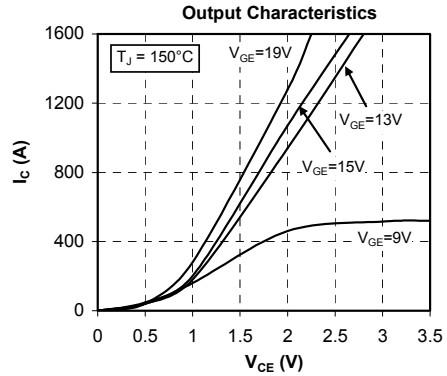
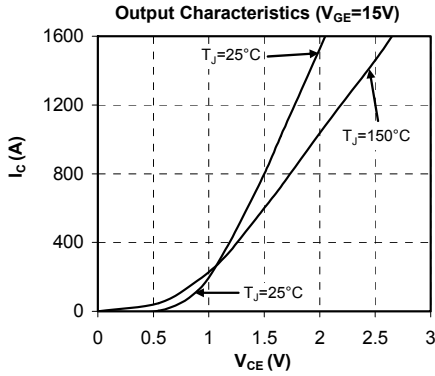
## Thermal and package characteristics

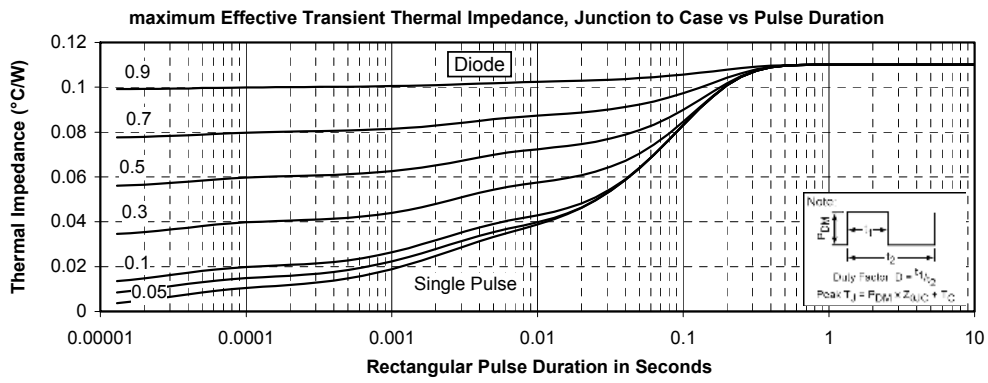
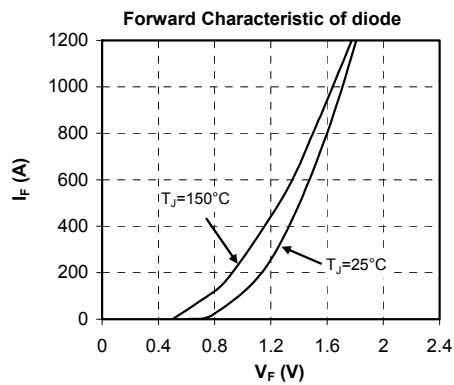
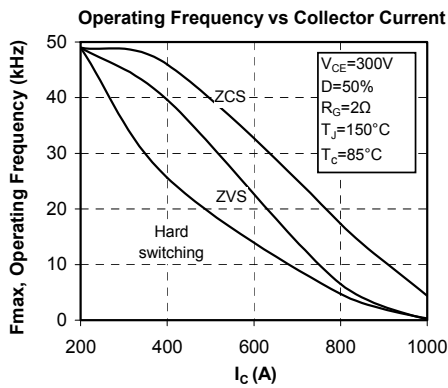
Symbol	Characteristic		Min	Typ	Max	Unit
R <sub>thJC</sub>	Junction to Case Thermal Resistance	IGBT			0.065	°C/W
		Diode			0.11	
V <sub>ISOL</sub>	RMS Isolation Voltage, any terminal to case t=1 min, 50/60Hz		4000			V
T <sub>J</sub>	Operating junction temperature range		-40		175	°C
T <sub>STG</sub>	Storage Temperature Range		-40		125	
T <sub>C</sub>	Operating Case Temperature		-40		125	
Torque	Mounting torque	M6	3		5	N.m
		M4	1		2	
Wt	Package Weight				350	g

### D4 Package outline (dimensions in mm)



## Typical Performance Curve





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